

AMENDMENTS TO THE SPECIFICATION

Amend the following paragraphs:

[0005] ~~DISCLOSURE~~ SUMMARY OF THE INVENTION

[0031] ~~BEST MODE FOR CARRYING OUT~~ DESCRIPTION OF THE INVENTION

Amend the Abstract:

[0047] Disclosed is a bipolar complementary metal oxide semiconductor (BiCMOS) or NPN/PNP device that has a collector (~~112~~), an intrinsic base (~~118~~) above the collector, shallow trench isolation regions (~~114~~) adjacent the collector, a raised extrinsic base (~~202~~) above the intrinsic base, a T-shaped emitter (~~800~~) above the extrinsic base, spacers (~~700~~) adjacent the emitter, and a silicide (~~400~~) layer that is separated from the emitter by the spacers.